



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

SS22F-SS210F-6AF

SMAF Schottky Barrier Rectifier Diode 肖特基势垒整流二极管



■Features 特点

Low forward voltage drop 低正向压降

High current capability 高电流能力

Surface mount device 表面贴装器件

Case 封装:SMAF



SMAF

■Maximum Rating 最大额定值

(T_A=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	SS22F -6AF	SS23F -6AF	SS24F -6AF	SS25F -6AF	SS26F -6AF	SS28F -6AF	SS29F -6AF	SS210F- 6AF	Unit 单位
Marking 印字		SS22	SS23	SS24	SS25	SS26	SS28	SS29	SS210	
Peak Reverse Voltage 反向峰值电压	V _{RRM}	20	30	40	50	60	80	90	100	V
DC Reverse Voltage 直流反向电压	V _R	20	30	40	50	60	80	90	100	V
RMS Reverse Voltage 反向电压均方根值	V _{R(RMS)}	14	21	28	35	42	56	63	70	V
Forward Rectified Current 正向整流电流	I _F	2								A
Peak Surge Current 峰值浪涌电流	I _{FSM}	50								A
Thermal Resistance J-L 结到管脚热阻	R _{θJL}	10								°C/W
Junction Temperature 结温	T _J	150								°C
Storage Temperature 储藏温度	T _{stg}	-65to+150°C								°C

■Electrical Characteristics 电特性

(T_A=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	SS22F-SS24F -6AF	SS25F-SS26F -6AF	SS28F-SS210F -6AF	Unit 单位	Condition 条件
Forward Voltage 正向电压	V _F	0.55	0.70	0.85	V	I _F =2A
Reverse Current 反向电流	I _R (25°C) (100°C)	0.1 5		0.02 2	mA	V _R =V _{RRM}
Diode Capacitance 二极管电容	C _D	170			pF	V _R =4V, f=1MHz

■ Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

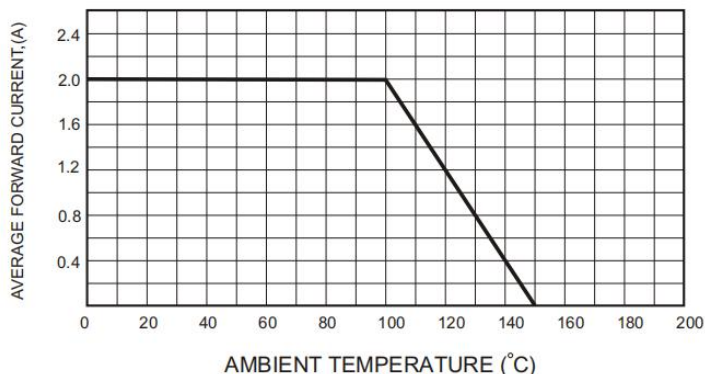


FIG.3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

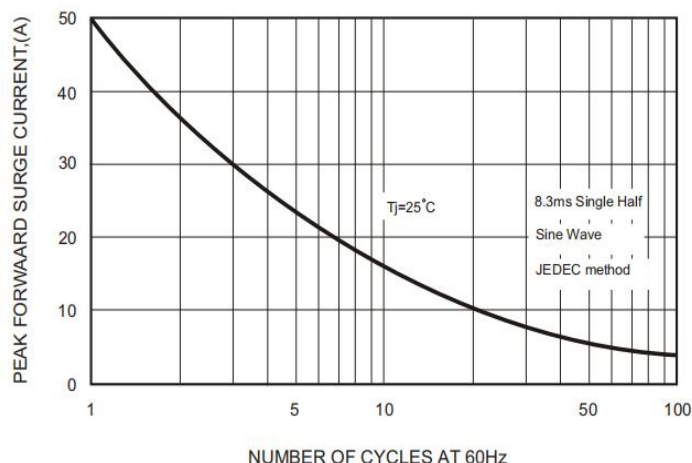


FIG.4-TYPICAL JUNCTION CAPACITANCE

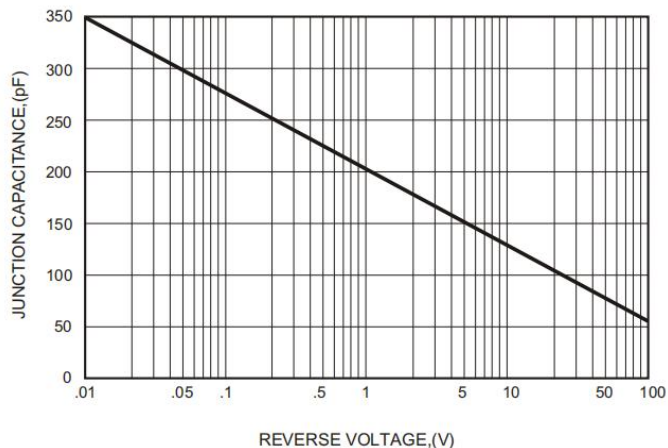


FIG.2-TYPICAL FORWARD CHARACTERISTICS

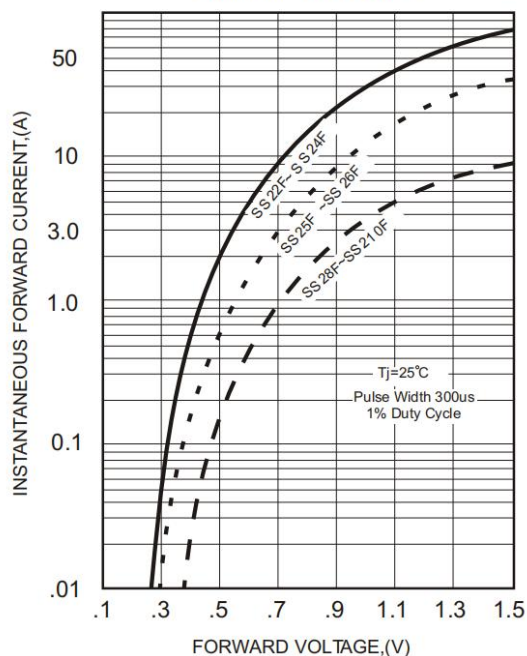
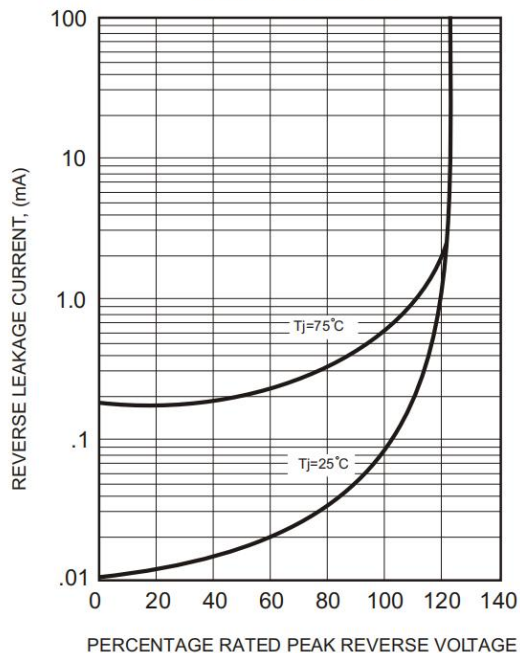
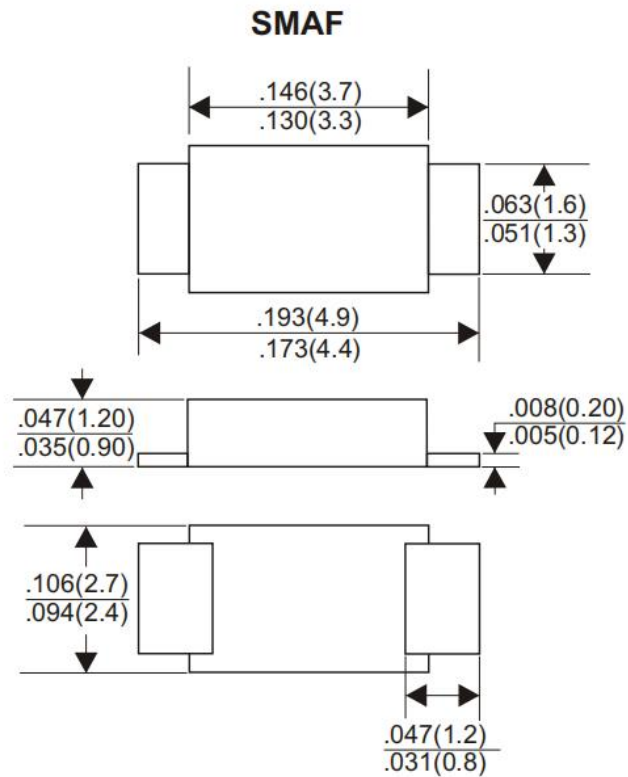


FIG.5 - TYPICAL REVERSE CHARACTERISTICS



■Dimension 外形封装尺寸



Dimensions in inches and (millimeters)